

EAST - [temp.wsp.1]

File View Edit Tools Window Help

☐ Drafts  
☐ Pending  
☒ Active

- L1: (16785) multilevel
- L2: (18492) multi adj2 level
- L3: (1901371) current
- L4: (1493450) third
- L5: (32439) 1 or 2
- L6: (37) 3 with 4 with 5
- L7: (201105) nitride
- L8: (2) 6 and 7
- L9: (501) trapping with 7
- L10: (13) 9 same 5
- L11: (14) sunkavalli-ravi-s.in.
- L12: (201113) 11 7
- L13: (6) 11 and 7
- L14: (6434) multi adj2 value
- L15: (0) 3 with 4 with 14
- L16: (64294) 3 with 4
- L23: (10) 16 and 14 and 7

☐ Failed  
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Search

DBs: USPAT, US-PGPUB, EPO, JPO, DERWENT, IB ☐ Plurals

Default operator: OR ☒ Highlight all hit terms initially

16 and 14 and 7

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20030043621 A1	20030306	24	Bit line reference circuits for bin 365/185.03			
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20020149061 A1	20021017	42	Nonvolatile memory cell, operating 257/365			
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20020149060 A1	20021017	42	Nonvolatile memory cell, operating 257/365			
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20020131309 A1	20020919	29	Memory, writing apparatus, reading 365/200			
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6424002 B1	20020723	37	Transistor, transistor array and no 257/316	257/317		
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6368293 B1	20020514	36	Nonvolatile memory cell, operating 257/365	257/324;		
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6144585 A	20001107	17	Semiconductor storage device for st 365/185.22	365/185.21		
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6040704 A	19990817	13	Method of manufacturing a reference 438/257	257/521 68.		

9:59 AM